

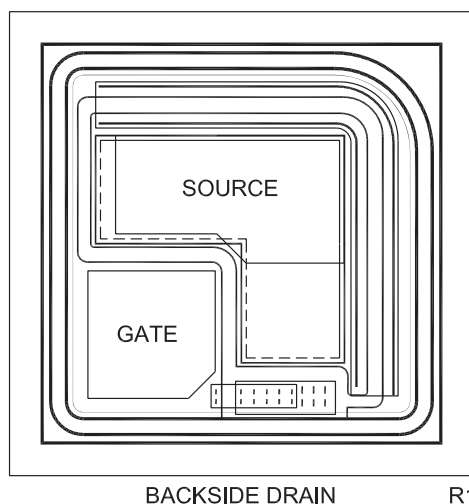
**PROCESS CP361R**  
**Small Signal MOSFET**  
N-Channel Enhancement-Mode MOSFET Chip



**PROCESS DETAILS**

|                         |                  |
|-------------------------|------------------|
| Die Size                | 14.2 x 14.2 MILS |
| Die Thickness           | 3.9 MILS         |
| Gate Bonding Pad Area   | 3.94 x 3.94 MILS |
| Source Bonding Pad Area | 3.94 x 7.08 MILS |
| Top Side Metalization   | Al-Si - 30,000Å  |
| Back Side Metalization  | Au - 12,000Å     |

**GEOMETRY**



**GROSS DIE PER 6 INCH WAFER**

123,000

**PRINCIPAL DEVICE TYPES**

CEDM7001

CMNDM7001

R1 (2-September 2010)

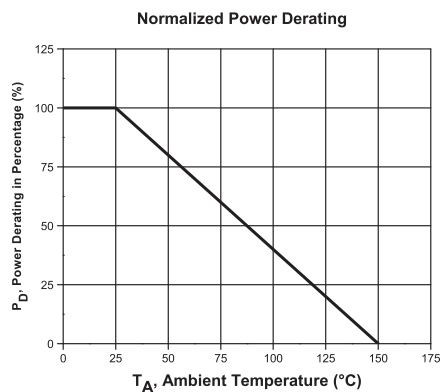
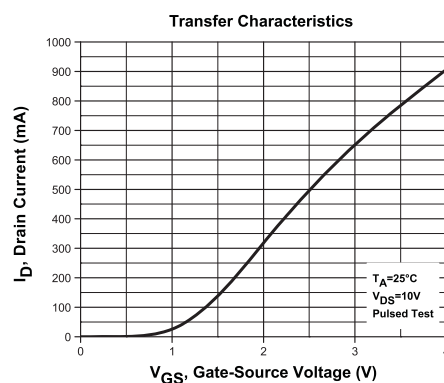
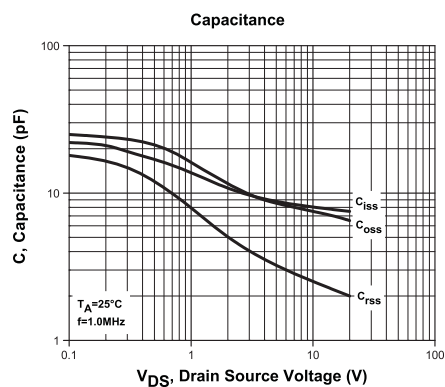
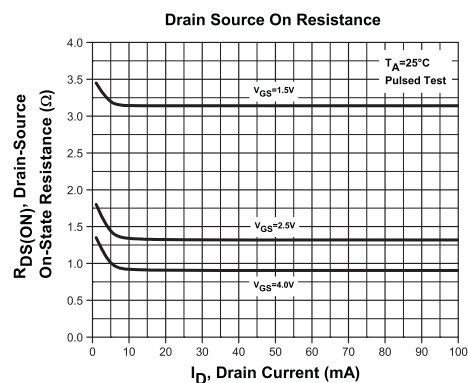
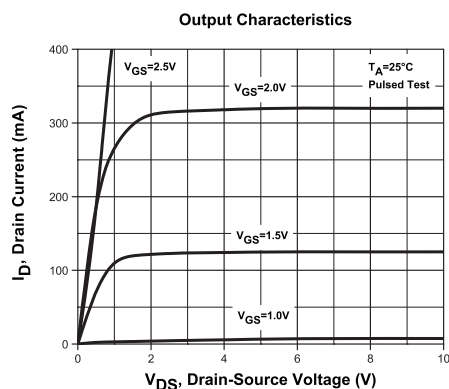
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# PROCESS CP361R

## Typical Electrical Characteristics



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